

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
MICRON.003C1APPLICATION NO.
09/037,945INFORMATION DISCLOSURE STATEMENT
BY APPLICANT

(USE SEVERAL SHEETS IF NECESSARY)

APPLICANT
Fazan et al.FILING DATE
March 10, 1998GROUP
2814

2823

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
G	4,243,435	01/06/81	Barile et al.	—	—	
G	4,247,343	01/27/81	Kruzhanov et al.	—	—	
G	4,290,184	09/22/81	Kuo	—	—	
G	4,551,910	11/12/85	Patterson	29	576	
G	4,979,803	12/25/90	McGuckin et al.	—	—	
G	5,134,089	7/28/92	Barden et al.	437	70	
G	5,151,381	9/29/92	Liu et al.	437	69	
G	5,218,214	06/08/93	Tyson et al.	—	—	
G	5,543,343	08/06/96	Bryant et al.	—	—	
G	5,637,528	06/10/97	Higashitani et al.	—	—	

RECEIVED

JUN 10 1999

FOREIGN PATENT DOCUMENTS TECHNOLOGY CENTER 2800

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
G	Kooi, et al., "Formation of Silicon Nitride at a Si-SiO ₂ Interface during Local Oxidation of Silicon and during Heat-Treatment of Oxidized Silicon in NH ₃ Gas", J. Electrochem Soc. SOLID-STATE SCIENCE AND TECHNOLOGY, July 1976, Vol. 123, No. 7, pgs. 1117-1120
G	Van Zant, Microchip Fabrication; A Practical Guide to Semiconductor Processing, McGraw-Hill, 1997, p. 159-160, 593.

EXAMINER	FOURSON	DATE CONSIDERED	1d/20/02
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.			